

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point	R_{thJS}	-	-	35	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint, t < 10s		-	-	110	
@ 6 cm ² cooling area ¹⁾		-	-	50	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0, I_D=-250\mu A$	$V_{(BR)DSS}$	-20	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=-250\mu A$	$V_{GS(th)}$	-0.6	-0.9	-1.2	
Zero gate voltage drain current $V_{DS}=-20V, V_{GS}=0, T_j=25^{\circ}C$ $V_{DS}=-20V, V_{GS}=0, T_j=150^{\circ}C$	I_{DSS}	- -	-0.1 -10	-1 -100	μA
Gate-source leakage current $V_{GS}=-12V, V_{DS}=0$	I_{GSS}	-	-10	-100	
Drain-source on-state resistance $V_{GS}=-2.5V, I_D=-11.9A$	$R_{DS(on)}$	-	9.8	12.9	m Ω
Drain-source on-state resistance $V_{GS}=-4.5, I_D=-14.9A$	$R_{DS(on)}$	-	7.2	8	

¹⁾ Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air; $t \leq 10$ sec.

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$ V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ $I_D = -11.9\text{A}$	32	64	-	S
Input capacitance	C_{iss}	$V_{GS}=0, V_{DS}=-15\text{V},$ $f=1\text{MHz}$	-	5962	-	pF
Output capacitance	C_{oss}		-	2168	-	
Reverse transfer capacitance	C_{rss}		-	781	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-10\text{V}, V_{GS}=-4.5\text{V},$ $I_D=-1\text{A}, R_G=6\Omega$	-	21.3	32	ns
Rise time	t_r		-	39.7	60	
Turn-off delay time	$t_{d(off)}$		-	108.5	163	
Fall time	t_f		-	127	190	

Gate Charge Characteristics

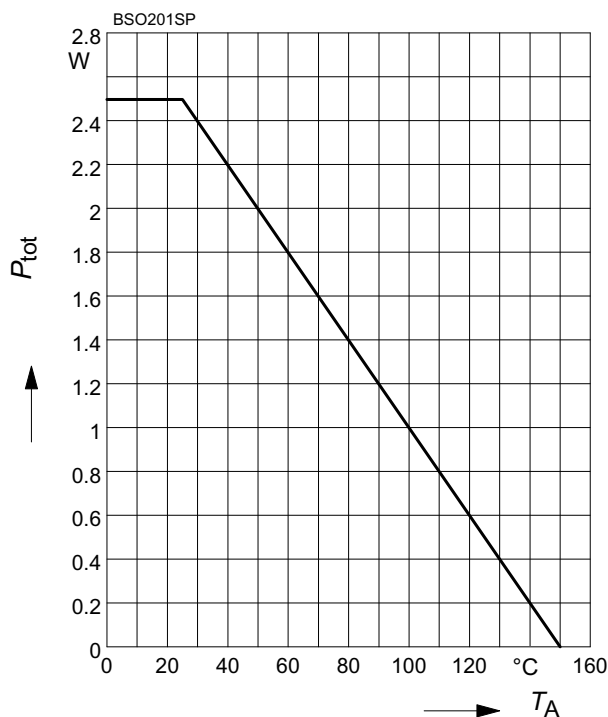
Gate to source charge	Q_{gs}	$V_{DD}=-15\text{V}, I_D=-14.9\text{A}$	-	-9.7	-14.5	nC
Gate to drain charge	Q_{gd}		-	-39.6	-59	
Gate charge total	Q_g	$V_{DD}=-15\text{V}, I_D=-14.9\text{A},$ $V_{GS}=0 \text{ to } -4.5\text{V}$	-	-85.5	-128	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD}=-15\text{V}, I_D=-14.9\text{A}$	-	-1.6	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_A=25^\circ\text{C}$	-	-	-3.7	A
Inverse diode direct current, pulsed	I_{SM}		-	-	-59.6	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0, I_F = I_D $	-	-0.8	-1.2	V
Reverse recovery time	t_{rr}	$V_R=-10\text{V}, I_F = I_D ,$ $di_F/dt=100\text{A}/\mu\text{s}$	-	62	77	ns
Reverse recovery charge	Q_{rr}		-	43	54	nC

1 Power dissipation

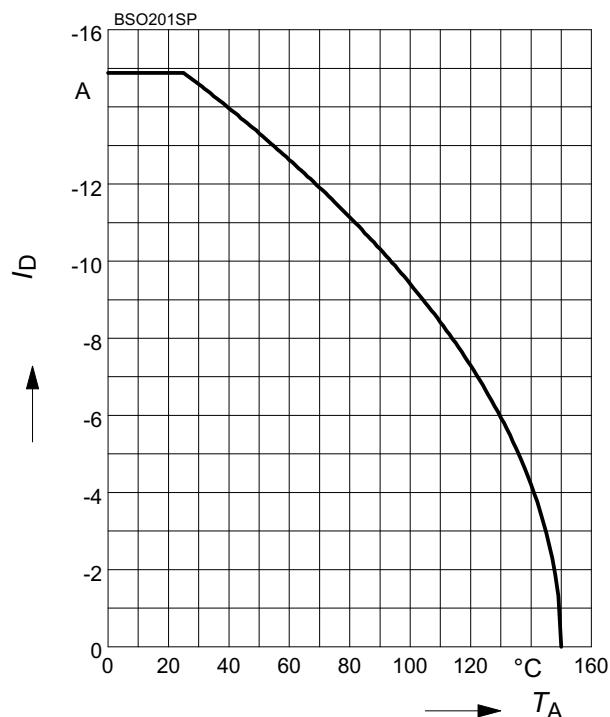
$$P_{\text{tot}} = f(T_A)$$



2 Drain current

$$I_D = f(T_A)$$

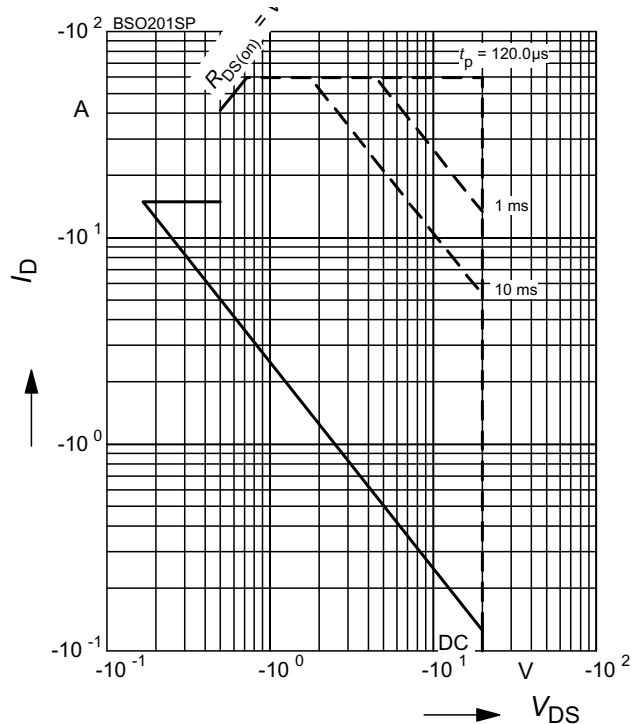
parameter: $|V_{GS}| \geq 4.5 \text{ V}$



4 Safe operating area

$$I_D = f(V_{DS})$$

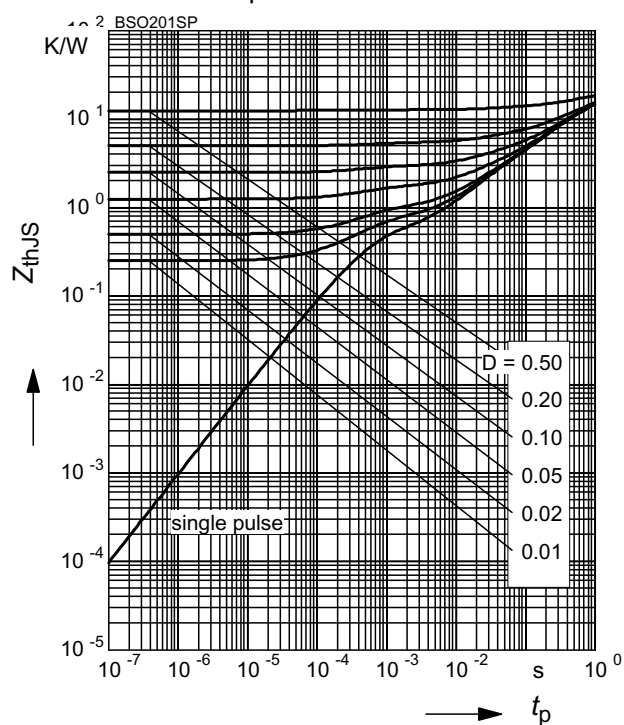
parameter: $D = 0$, $T_A = 25^\circ\text{C}$



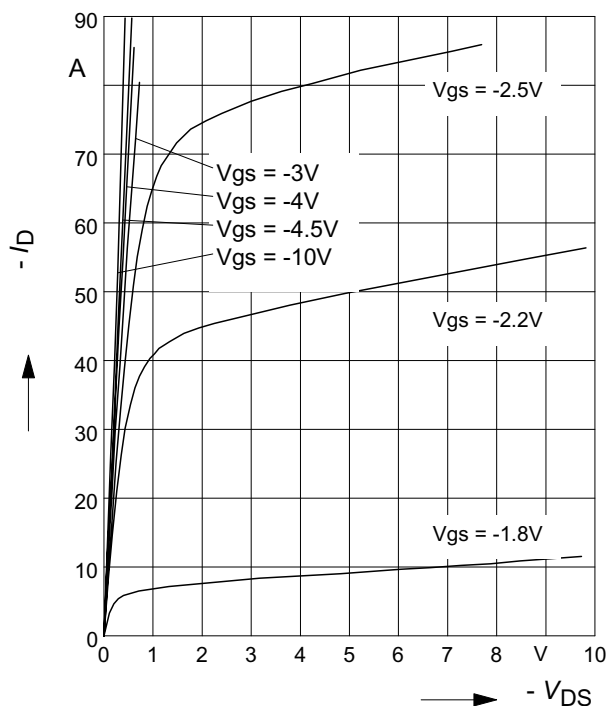
3 Transient thermal impedance

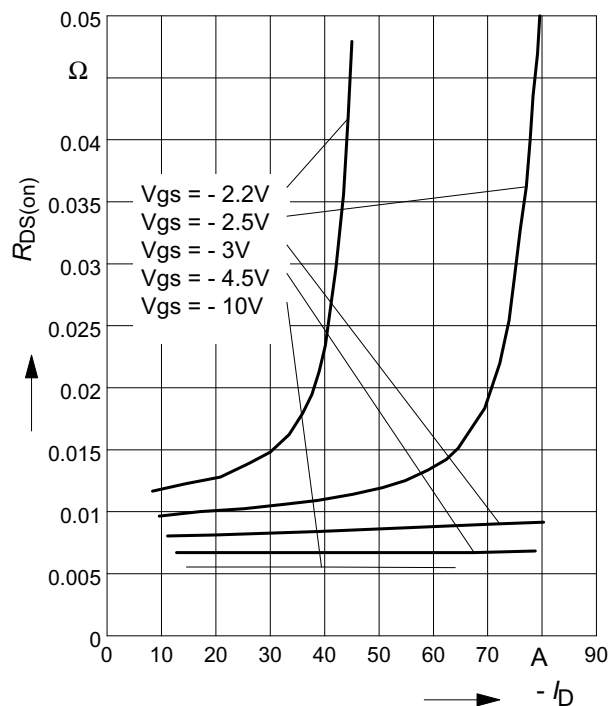
$$Z_{\text{thJS}} = f(t_p)$$

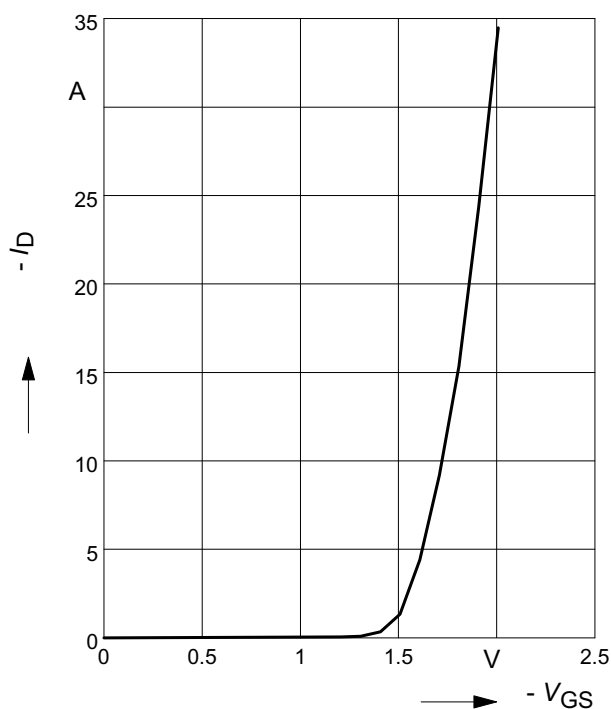
parameter: $D = t_p/T$

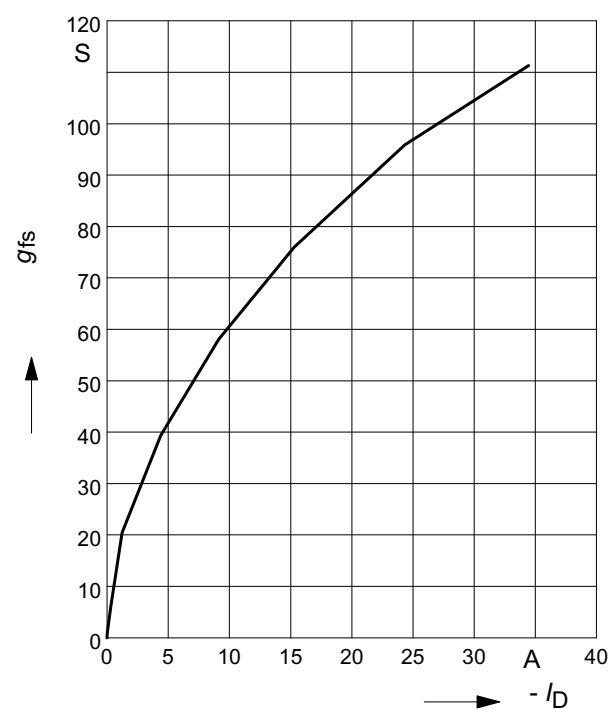


5 Typ. output characteristic
 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

parameter: $t_p = 80 \mu\text{s}$

6 Typ. drain-source on resistance
 $R_{DS(on)} = f(I_D)$

parameter: V_{GS}

7 Typ. transfer characteristics
 $I_D = f(V_{GS}); |V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$

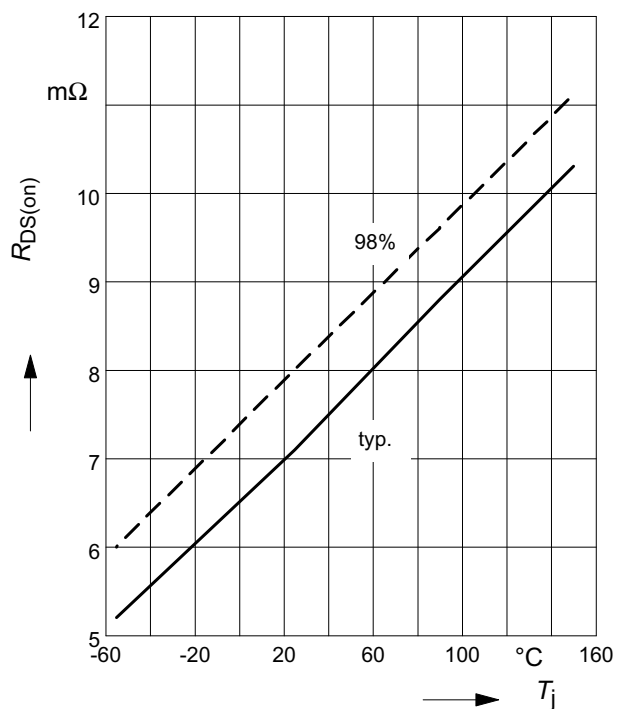
parameter: $t_p = 80 \mu\text{s}$

8 Typ. forward transconductance
 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

parameter: $t_p = 80 \mu\text{s}$


9 Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

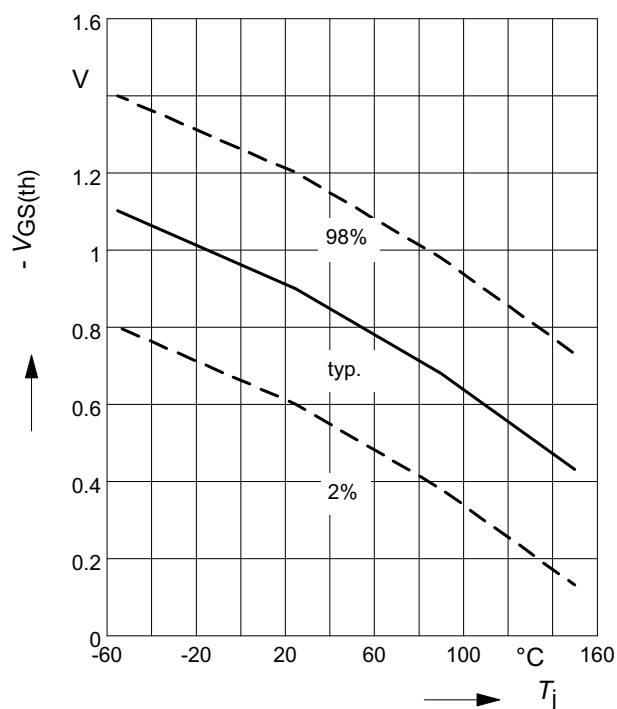
parameter: $I_D = -14.9 \text{ A}$, $V_{GS} = -4.5 \text{ V}$



10 Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

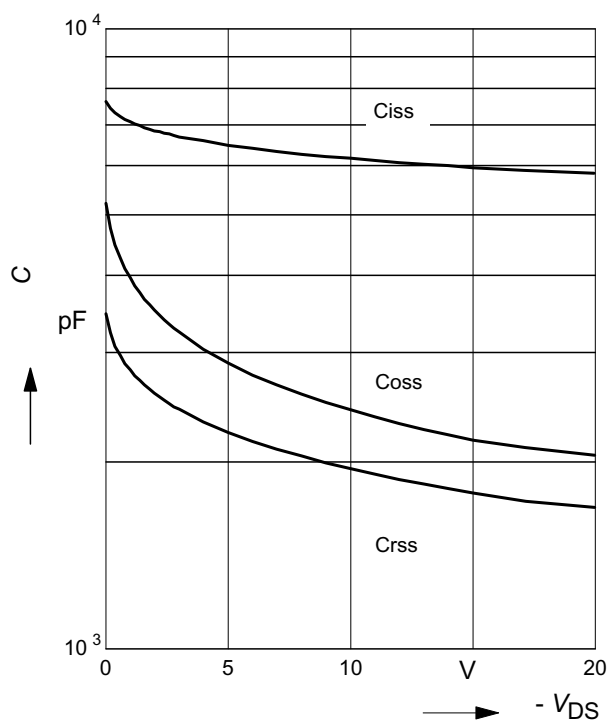
parameter: $V_{GS} = V_{DS}$, $I_D = -250 \mu\text{A}$



11 Typ. capacitances

$$C = f(V_{DS})$$

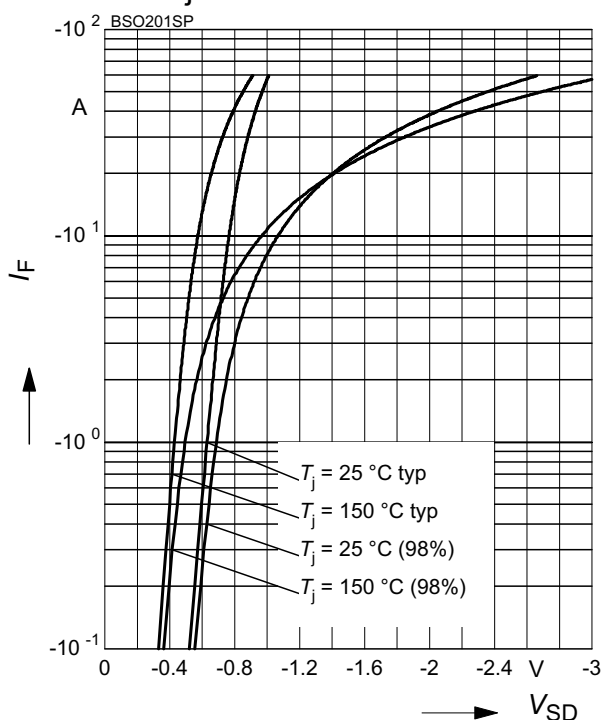
parameter: $V_{GS}=0$, $f=1 \text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

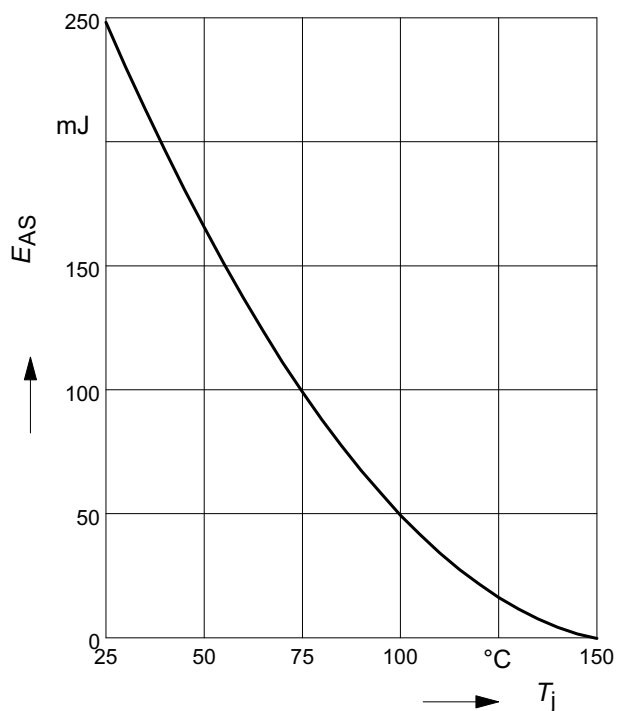
parameter: T_j , $t_p = 80 \mu\text{s}$



13 Typ. avalanche energy

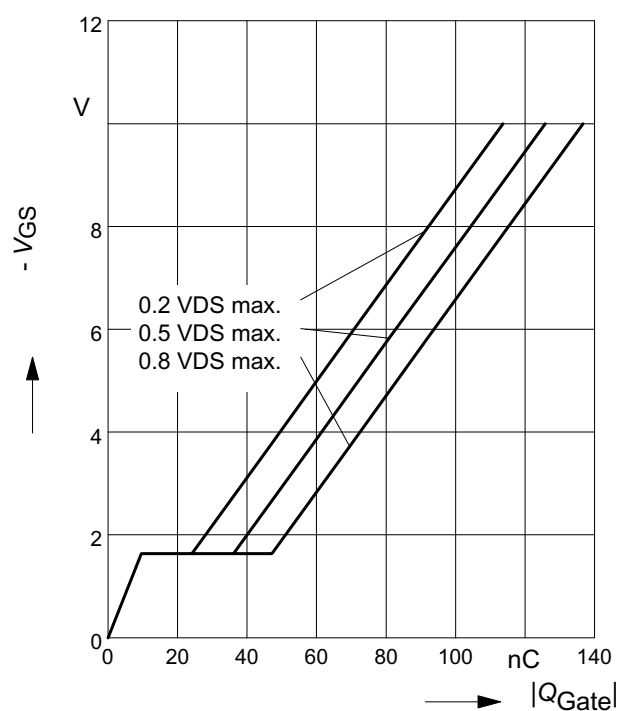
$$E_{AS} = f(T_j), \text{ par.: } I_D = -14.9 \text{ A}$$

$$V_{DD} = -10 \text{ V}, R_{GS} = 25 \Omega$$

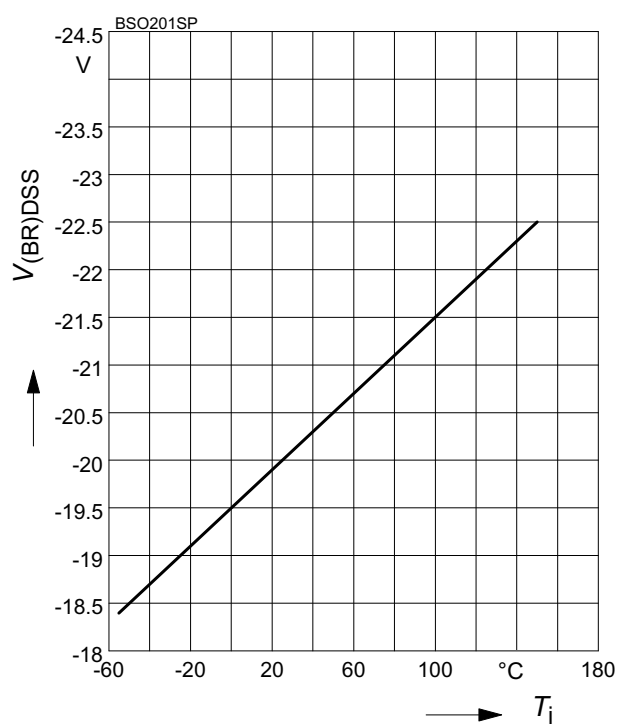

14 Typ. gate charge

$$|V_{GS}| = f(Q_{Gate})$$

$$\text{parameter: } I_D = -14.9 \text{ A pulsed}$$


15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



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